WEST Search History

Hide Items Restore Clear Cancel

DATE: Monday, September 27, 2004

Hide?	<u>Set Name</u>	<u>Query</u>	Hit Count
	DB=PGPB, USA	PT,USOC,EPAB,JPAB,DWPI,TDBD; PL	UR=YES; OP=ADJ
	L7	L6 and alcohols	4
	L6	L5 and placing	4
\Box	L5	L4 and wafer	9
	L4	L3 and (stripping solution)	10
	L3	L2 and (metal line)	447
	L2	L1 and removing	56546
	L1	residues and polymer	189812

END OF SEARCH HISTORY

Hit List

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 4 of 4 returned.

1. Document ID: US 20040050406 A1

Using default format because multiple data bases are involved.

L7: Entry 1 of 4

File: PGPB

Mar 18, 2004

PGPUB-DOCUMENT-NUMBER: 20040050406

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040050406 A1

TITLE: Compositions and method for removing photoresist and/or resist residue at

pressures ranging from ambient to supercritical

PUBLICATION-DATE: March 18, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Sehgal, Akshey

Eagle

ID

US

US-CL-CURRENT: <u>134/26</u>; <u>510/175</u>, <u>510/176</u>, <u>510/201</u>

Full Title Citation Front Review Classification Date Refe	erence Sequences	Attachments	Claims KMC Draw
		-	

2. Document ID: US 20040011386 A1

L7: Entry 2 of 4

File: PGPB

Jan 22, 2004

PGPUB-DOCUMENT-NUMBER: 20040011386

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040011386 A1

TITLE: Composition and method for removing photoresist and/or resist residue using

supercritical fluids

PUBLICATION-DATE: January 22, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Seghal, Akshey

Eagle

ID

US

US-CL-CURRENT: <u>134/26</u>; <u>510/175</u>, <u>510/505</u>

ABSTRACT:

hebbgeeef e e ef be

A method of <u>removing</u> photoresist and/or resist <u>residue</u> from a substrate includes exposing the substrate to a supercritical fluid in combination with a co-solvent mixture comprising an organic solvent and an oxidizer. In one embodiment, the supercritical fluid is supercritical carbon dioxide and the co-solvent mixture includes 1,2-Butylene Carbonate, Dimethyl Sulfoxide and hydrogen peroxide. If desired, supercritical carbon dioxide in combination with a second co-solvent mixture may be subsequently applied to the substrate to rinse and dry the substrate. In one embodiment, the second co-solvent mixture includes isopropyl alcohol.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KMC | Draw De

3. Document ID: US 20020013240 A1

L7: Entry 3 of 4

File: PGPB

Jan 31, 2002

PGPUB-DOCUMENT-NUMBER: 20020013240

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20020013240 A1

TITLE: COMPOSITION AND METHOD FOR REMOVING RESIST AND ETCHING RESIDUES USING

HYDROXYLAMMONIUM CARBOXYLATES

PUBLICATION-DATE: January 31, 2002

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

SAHBARI, JAVAD J.

SUNNYVALE

CA

US

US-CL-CURRENT: 510/176; 216/100, 252/79.4, 510/109, 510/401

ABSTRACT:

A mixture of hydroxylamine partially neutralized with a weak carboxylic acid and an organic solvent such as an alkyl sulfoxide, a pyrrolidinone or a sulfone removes hardened photoresist and polymeric photoresist <u>residues</u> from a substrate with reduced metal corrosion.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWC | Draw, De

4. Document ID: US 6432209 B1

L7: Entry 4 of 4

File: USPT

Aug 13, 2002

US-PAT-NO: 6432209

DOCUMENT-IDENTIFIER: US 6432209 B1

TITLE: Composition and method for removing resist and etching residues using

hydroxylazmmonium carboxylates

DATE-ISSUED: August 13, 2002

h eb bgeeef e e ef b e

INVENTOR-INFORMATION:

NAME

CITY

STATE

ZIP CODE

COUNTRY

Sahbari; Javad J.

Sunnyvale

CA

US-CL-CURRENT: <u>134/3</u>; <u>510/176</u>

ABSTRACT:

A mixture of hydroxylamine partially neutralized with a weak carboxylic acid and an organic solvent such as an alkyl sulfoxide, a pyrrolidinone or a sulfone removes hardened photoresist and polymeric photoresist <u>residues</u> from a substrate with reduced metal corrosion.

1 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full	Fitte Citation Front Review Classification Date Reference	Claims KMC D
lear	Generate Collection Print Fwd Refs Bkwd Refs	Generate OACS
	Term	Documents
	ALCOHOLS	354705
i	ALCOHOL	801784
	(6 AND ALCOHOLS).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD.	4.
	(L6 AND ALCOHOLS).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD.	4

Display Format: - Change Format

<u>Previous Page</u> <u>Next Page</u> <u>Go to Doc#</u>

Hit List

Clear Generate Collection Print Fwd Refs Bkwd Refs
Generate OACS

Search Results - Record(s) 1 through 10 of 10 returned.

1. Document ID: US 20040050406 A1

Using default format because multiple data bases are involved.

L4: Entry 1 of 10

File: PGPB

Mar 18, 2004

PGPUB-DOCUMENT-NUMBER: 20040050406

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040050406 A1

TITLE: Compositions and method for removing photoresist and/or resist residue at

pressures ranging from ambient to supercritical

PUBLICATION-DATE: March 18, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Sehgal, Akshey

Eagle

ID

US

US-CL-CURRENT: <u>134/26</u>; <u>510/175</u>, <u>510/176</u>, <u>510/201</u>

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWC | Drawt De

2. Document ID: US 20040011386 A1

L4: Entry 2 of 10

File: PGPB

Jan 22, 2004

PGPUB-DOCUMENT-NUMBER: 20040011386

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20040011386 A1

TITLE: Composition and method for removing photoresist and/or resist residue using

supercritical fluids

PUBLICATION-DATE: January 22, 2004

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Seghal, Akshey

Eagle

ID

US

US-CL-CURRENT: <u>134/26</u>; <u>510/175</u>, <u>510/505</u>

ABSTRACT:

h eb b g ee ef b e

A method of <u>removing</u> photoresist and/or resist <u>residue</u> from a substrate includes exposing the substrate to a supercritical fluid in combination with a co-solvent mixture comprising an organic solvent and an oxidizer. In one embodiment, the supercritical fluid is supercritical carbon dioxide and the co-solvent mixture includes 1,2-Butylene Carbonate, Dimethyl Sulfoxide and hydrogen peroxide. If desired, supercritical carbon dioxide in combination with a second co-solvent mixture may be subsequently applied to the substrate to rinse and dry the substrate. In one embodiment, the second co-solvent mixture includes isopropyl alcohol.

Full: Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KMC | Draw De

3. Document ID: US 20030140948 A1

L4: Entry 3 of 10

File: PGPB

Jul 31, 2003

PGPUB-DOCUMENT-NUMBER: 20030140948

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20030140948 A1

TITLE: Clean equipment for removing polymer residues on sidewalls of metal lines

and method thereof

PUBLICATION-DATE: July 31, 2003

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Ni, Chih-Jung

Hsin-Chu

тw

Jan, Jia-Shing

Taipei City

TW

US-CL-CURRENT: <u>134/26</u>; <u>134/102</u>.1, 134/61

ABSTRACT:

A clean equipment for removing polymer residues on sidewalls of metal lines and method thereof are provided. The present clean equipment comprises a stripping solution bath, at least an organic solvent bath, an overflow bath and a dryer. A gas bubbler and a lattice-like cassette stage are positioned within the organic solvent bath. The gas bubbler provides gas flow in the organic solvent bath to increase the convection of the organic solvent. The lattice-like cassette stage is used for supporting cassettes for carrying wafers. By way of increasing the number of bubbling apertures of the gas bubbler and designing the gas bubbler structure in a way that preventing the bubbling apertures from being blocked by the lattice-like cassette stage, the convection effectiveness of the organic solvent is increased. Thereby, the stripping solution can be effectively removed with the organic solvent. Besides, lengthening the drip dry time of the wafer over each bath so as to eliminate the quantity of the stripping solution left on the wafer drawn in the overflow bath. By the above measures, metal corrosion occurred on the sidewalls of the metal lines formed on the wafer is significantly reduced.

Full Title Citation Front Review Classification Date Reference Sequences Attachments Claims KodC Draw De

4. Document ID: US 20020013240 A1

L4: Entry 4 of 10

File: PGPB

Jan 31, 2002

PGPUB-DOCUMENT-NUMBER: 20020013240

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20020013240 A1

TITLE: COMPOSITION AND METHOD FOR REMOVING RESIST AND ETCHING RESIDUES USING

HYDROXYLAMMONIUM CARBOXYLATES

PUBLICATION-DATE: January 31, 2002

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

SAHBARI, JAVAD J.

SUNNYVALE

CA

US

US-CL-CURRENT: 510/176; 216/100, 252/79.4, 510/109, 510/401

ABSTRACT:

A mixture of hydroxylamine partially neutralized with a weak carboxylic acid and an organic solvent such as an alkyl sulfoxide, a pyrrolidinone or a sulfone removes hardened photoresist and polymeric photoresist <u>residues</u> from a substrate with reduced metal corrosion.

-	Full Title Citation Front Review	Classification	Date	Reference	Sequences	Attachments	Claims	KMC Draw	7
									-

5. Document ID: US 20020013239 A1

L4: Entry 5 of 10

File: PGPB

Jan 31, 2002

PGPUB-DOCUMENT-NUMBER: 20020013239

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20020013239 A1

TITLE: Polymer remover

PUBLICATION-DATE: January 31, 2002

INVENTOR-INFORMATION:

NAME

CITY

STATE

COUNTRY

RULE-47

Sahbari, Javad J.

Sunnyvale

CA

US

US-CL-CURRENT: $\underline{510}/\underline{175}$; $\underline{257}/\underline{E21.255}$, $\underline{257}/\underline{E21.313}$, $\underline{510}/\underline{407}$, $\underline{510}/\underline{412}$, $\underline{510}/\underline{413}$, $\underline{510}/\underline{505}$

ABSTRACT:

Disclosed are compositions and methods useful for the removal of polymeric material from substrates, such as electronic devices. The compositions and methods of the

h eb bgeeef e e ef b

present invention are particularly suitable for <u>removing polymer residues</u> from electronic devices following plasma etch processes.

Full: | Title: | Citation | Front: | Review | Classification | Date | Reference | Sequences | Attachments: | Citatins | KWIC: | Drawt De

6. Document ID: US 6554912 B2

L4: Entry 6 of 10

File: USPT

Apr 29, 2003

US-PAT-NO: 6554912

DOCUMENT-IDENTIFIER: US 6554912 B2

TITLE: Polymer remover

DATE-ISSUED: April 29, 2003

INVENTOR-INFORMATION:

NAME

CITY

STATE

ZIP CODE

COUNTRY

Sahbari; Javad J.

Sunnyvale

CA

ABSTRACT:

Compositions for the removal of polymeric material from a substrate are provided where the compositions include a polyol compound selected from (C.sub.3 -C.sub.20) alkanediols, substituted (C.sub.3 -C.sub.20) alkanediols, (C.sub.3 -C.sub.20) alkanetriols or substituted (C.sub.3 -C.sub.20) alkanetriols, a glyco ether, at least 5% wt water based on the total weight of the composition, and a fluoride salt selected from ammonium fluoride, ammonium bifluoride, ammonium-tetramethylammonium bifluoride or mixtures thereof. Methods of removing polymeric material using these compositions are also provided.

14 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full Title Citation Front Review Classification Date Reference	Claims KMC Draw De
Date: Releience	-Citalinis ::::K00Cis ::::Df300, De

7. Document ID: US 6432209 B1

L4: Entry 7 of 10

File: USPT

Aug 13, 2002

US-PAT-NO: 6432209

DOCUMENT-IDENTIFIER: US 6432209 B1

TITLE: Composition and method for removing resist and etching residues using

hydroxylazmmonium carboxylates

DATE-ISSUED: August 13, 2002

h eb bgeeef e e ef b e

INVENTOR-INFORMATION:

NAME

CITY

STATE ZIP CODE COUNTRY

Sahbari; Javad J.

Sunnyvale

CA

US-CL-CURRENT: <u>134/3</u>; <u>510/176</u>

ABSTRACT:

A mixture of hydroxylamine partially neutralized with a weak carboxylic acid and an organic solvent such as an alkyl sulfoxide, a pyrrolidinone or a sulfone removes hardened photoresist and polymeric photoresist residues from a substrate with reduced metal corrosion.

1 Claims, 0 Drawing figures Exemplary Claim Number: 1

Full Title Citation	Front Review	Classification	Date	Reference	Claims KWC Draw De
	3.5.				
••••••••••••••••••••••••••••••••••••	***************************************			······	 ······

8. Document ID: US 6107202 A

L4: Entry 8 of 10

File: USPT

Aug 22, 2000

US-PAT-NO: 6107202

DOCUMENT-IDENTIFIER: US 6107202 A

TITLE: Passivation photoresist stripping method to eliminate photoresist extrusion

after alloy

DATE-ISSUED: August 22, 2000

INVENTOR-INFORMATION:

NAME

CITY

STATE

ZIP CODE

COUNTRY

Chiu; Chih-Kang

Yung-Ho

тw

Pan; Sheng-Liang

Hsin-Chu

TW

US-CL-CURRENT: 438/690; 257/E21.255, 257/E21.581, 438/120, 438/618, 438/700, <u>438/750</u>, <u>438/781</u>, <u>438/906</u>, <u>438/948</u>, <u>438/963</u>

ABSTRACT:

A method for stripping positive photoresist from a keyhole 17 in a passivation layer 18 before a heating process using NMP solvent strips after a photoresist strip. The process is summarized by the 5 steps as follows: (1) Photoresist strip 1 (e.g., EKC 830), (2) Photoresist strip 2 (e.g., EKC 830 photoresist stripper), (3) N-methly-2-pyrolidone (NMP) solvent strip-agitated (solvent is preferably the same solvent in the photoresist stripper (1 &2) (4) NMP solvent strip-agitated and (5) H.sub.2 O rinse. The NMP solvent strip steps (3) and (4) remove photoresist residue (16, FIG. 1) in the key hole 17. This prevents the formation of photoresist extrusions 24 while annealing the metal lines 14.

16 Claims, 3 Drawing figures Exemplary Claim Number: 15 Number of Drawing Sheets: 2

Full Title Citation Front Review Classification Date Reference Claims KMCC Draw De

9. Document ID: US 20030140948 A1

L4: Entry 9 of 10

File: DWPI

Jul 31, 2003

DERWENT-ACC-NO: 2003-607241

DERWENT-WEEK: 200357

COPYRIGHT 2004 DERWENT INFORMATION LTD

TITLE: Cleaning equipment for $\underline{\text{removing polymer residues}}$, such as metal corrosion, on sidewalls of $\underline{\text{metal lines}}$ formed on wafer, has dryer for drying water left on

wafer after water flow is provided on wafer by overflow bath

INVENTOR: JAN, J; NI, C

PRIORITY-DATA: 2002US-0057906 (January 29, 2002)

PATENT-FAMILY:

PUB-NO

PUB-DATE

LANGUAGE

PAGES

MAIN-IPC

US 20030140948 A1

July 31, 2003

013

B08B003/04

INT-CL (IPC): $\underline{B08} \ \underline{B} \ \underline{3/04}$; $\underline{B08} \ \underline{B} \ \underline{3/08}$; $\underline{B08} \ \underline{B} \ \underline{3/10}$

10. Document ID: US 6107202 A

L4: Entry 10 of 10

File: DWPI

Aug 22, 2000

DERWENT-ACC-NO: 2000-646373

DERWENT-WEEK: 200062

COPYRIGHT 2004 DERWENT INFORMATION LTD

TITLE: Process for stripping photoresist in semiconductor manufacture involves forming metal pattern, passivation layer sequentially on semiconductor, developing photoresist pattern and etching passivation layer

INVENTOR: CHIU, C; PAN, S

PRIORITY-DATA: 1998US-0152349 (September 14, 1998)

PATENT-FAMILY:

PUB-NO

PUB-DATE

LANGUAGE

PAGES

MAIN-IPC

US 6107202 A

August 22, 2000

010

H01L021/308

INT-CL (IPC): H01 L 21/308

Full of Title of Citation of Front of Review of Classification of Date of Reference of Citation of Front of Review of Classification of Date of Reference of Citation of Citat

h eb b g ee ef b

Гегт	Documents
STRIPPING	147628
STRIPPINGS	417
SOLUTION	4524063
SOLN	446455
SOLNS	52719
SOLUTIONS	676088
(3 AND (STRIPPING ADJ SOLUTION)).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD.	10
L3 AND (STRIPPING SOLUTION)).PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD.	10

Display Format: - Change Format

Previous Page Next Page

Go to Doc#

е